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PATENT NUMBER and
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM 10085903	FILING DATE 02 28 2002	CLASS 257	SUBCLASS	GAU 2875	EXAMINER
**APPLICANTS: Wei Andy, Sultan Akif, Wu David					
**CONTINUING DATA VERIFIED:					
** FOREIGN APPLICATIONS VERIFIED:					
PG-PUB <input type="checkbox"/> DO NOT PUBLISH <input checked="" type="checkbox"/>		RESCIND <input type="checkbox"/>			
Foreign priority claimed <input type="checkbox"/> yes <input checked="" type="checkbox"/> no 35 USC 119 conditions met <input type="checkbox"/> yes <input checked="" type="checkbox"/> no Verified and Acknowledged Examination <input type="checkbox"/> yes <input checked="" type="checkbox"/> no				ATTORNEY DOCKET NO AMDI 115 HON	
TITLE : SOI mosfet junction degradation using multiple buried amorphous layers					

NOTICE OF ALLOWANCE MAILED		Assistant Examiner	CLAIMS ALLOWED	
			Total Claims	Print Claim for O.G.
ISSUE FEE		Primary Examiner	DRAWING	
Amount Due	Date Paid		Sheets Drwg.	Figs. Drwg.
<input type="checkbox"/> TERMINAL DISCLAIMER		PREPARED FOR ISSUE	Application Examiner	
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